N-Channel 200 V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	200	
$R_{DS(on)}$ (Ω)	V_{GS} = 10 V	0.8
Q_g (Max.) (nC)	4.8	
Q_{gs} (nC)	0.56	
Q_{gd} (nC)	1.3	
Configuration	Single	

FEATURES

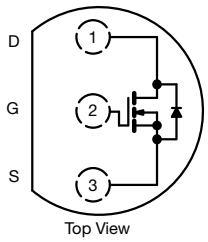
- Low On-Resistance
- Secondary Breakdown Free
- Low Power/Voltage Driven
- Low Input and Output Leakage
- Excellent Thermal Stability

Pb-free
RoHS COMPLIANT
HALOGEN FREE Available

APPLICATIONS

- High-Voltage Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Transistors, etc.
- Telephone Mute Switches, Ringer Circuits
- Power Supply, Converters
- Motor Control

TO-92



Top View

BENEFITS

- Low Offset Voltage
- Full-Voltage Operation
- Easily Driven Without Buffer
- Low Error Voltage
- No High-Temperature “Run-Away”

ABSOLUTE MAXIMUM RATINGS T_C = 25 °C, unless otherwise noted

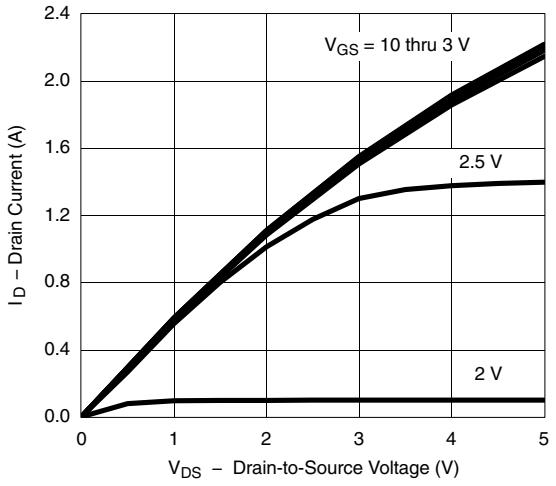
PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V_{DS}	200	V
Gate-Source Voltage			V_{GS}	± 20	
Continuous Drain Current	V_{GS} at 10 V	T_C = 25 °C	I_D	0.6	A
		T_C = 70 °C		0.4	
Pulsed Drain Current[a]			I_{DM}	2.4	
Linear Derating Factor				0.33	W/°C
Linear Derating Factor (PCB Mount)				0.020	
Single Pulse Avalanche Energy			E_{AS}	54	mJ
Repetitive Avalanche Current			I_{AR}	1.0	A
Repetitive Avalanche Energy			E_{AR}	2.2	mJ
Maximum Power Dissipation	T_A = 25 °C		P_D	1.6	W
Maximum Power Dissipation (PCB Mount)	T_A = 75 °C			1.2	
Peak Diode Recovery dV/dt			dV/dt	3.0	V/ns
Operating Junction and Storage Temperature Range			T_J, T_{stg}	- 55 to + 150	°C
Soldering Recommendations (Peak Temperature)	for 10 s			260[d]	

SPECIFICATIONS (T_A = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Limits**			
			Min.	**Typ.[a]**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 100 µA	200			V
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	0.8	1.65	2	
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 192 V, V_{GS} = 0 V			1	µA
		V_{DS} = 192 V, V_{GS} = 0 V, T_J = 55 °C			10	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} = 10 V, V_{GS} = 10 V	0.8			A
		V_{DS} = 10 V, V_{GS} = 4.5 V	0.5			
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 0.6 A		0.8		Ω
		V_{GS} = 4.5 V, I_D = 0.5 A		1.0		
		V_{GS} = 2.5 V, I_D = 0.3 A		1.6		
Forward Transconductance[a]	g_{fs}	V_{DS} = 10 V, I_D = 0.6 A		1.6		S
Diode Forward Voltage	V_{SD}	V_{GS} = 0 V, I_S = 0.6 A		0.8	1.2	V
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = 192 V, V_{GS} = 10 V, I_D = 0.5 A		4.87	8	nC
Gate-Source Charge	Q_{gs}			0.56		
Gate-Drain Charge	Q_{gd}			1.53		
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 60 V, R_L = 200 Ω I_D ≅ 0.3 A, V_{GEN} = 10 V, R_g = 25 Ω		5	10	ns
Rise Time	t_r			12	20	
Turn-Off Delay Time	$t_{d(off)}$			35	60	
Fall Time	t_f			16	25	

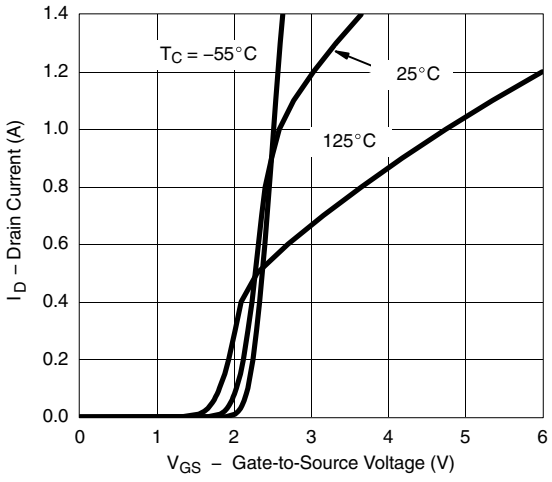
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

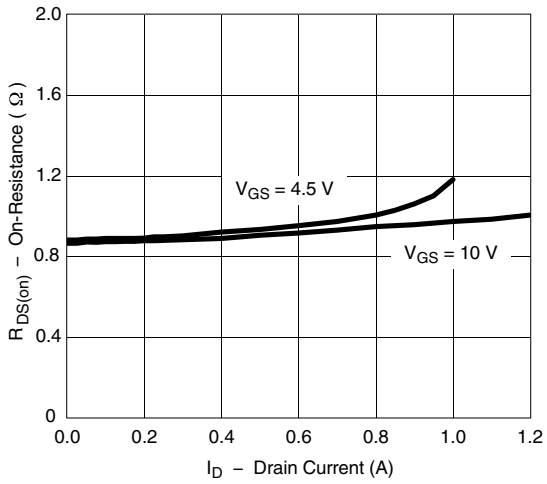
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



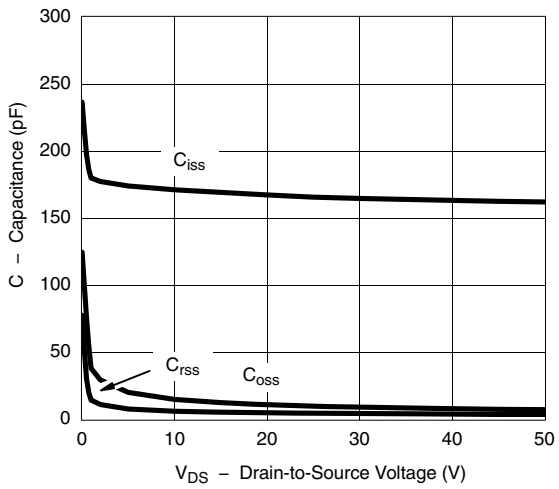
Output Characteristics



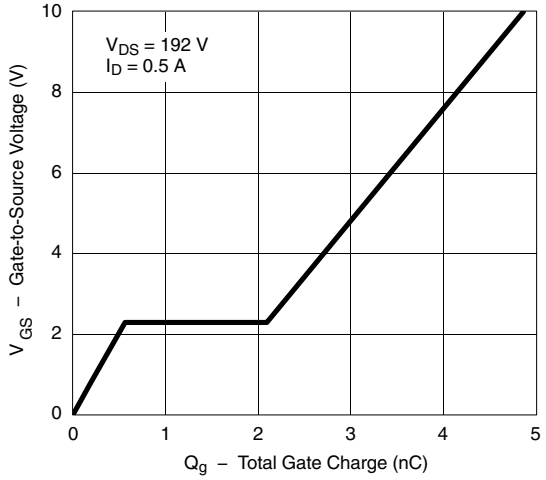
Transfer Characteristics



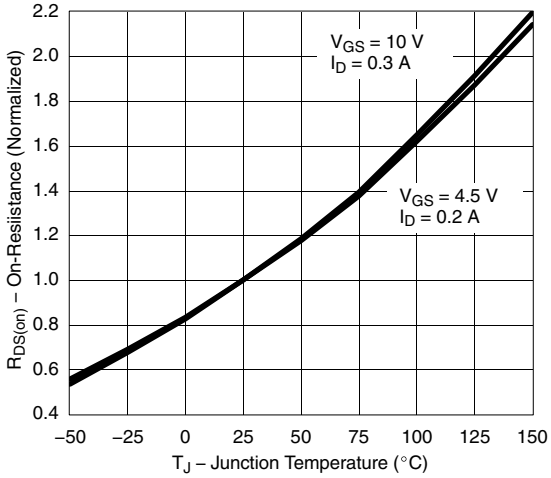
On-Resistance vs. Drain Current



Capacitance

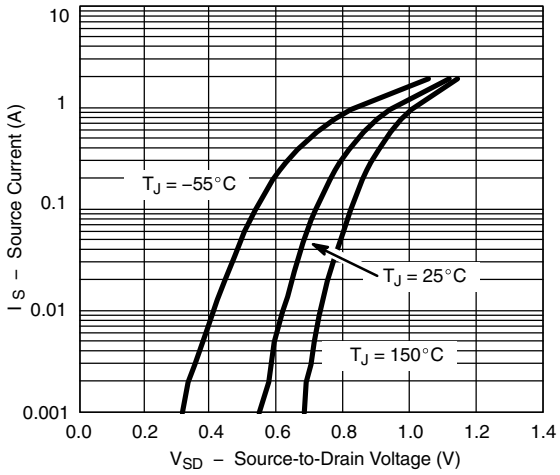


Gate Charge

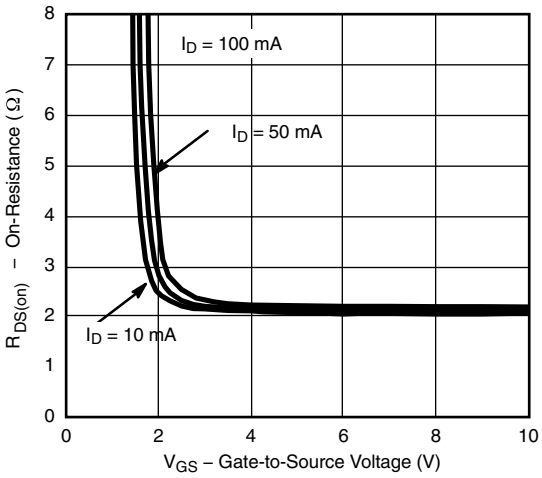


On-Resistance vs. Junction Temperature

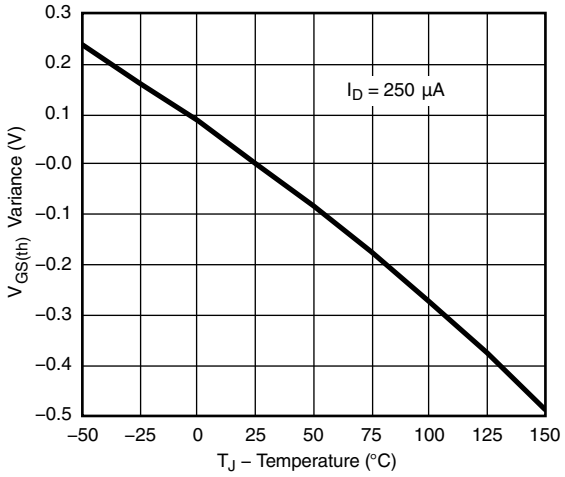
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Source-Drain Diode Forward Voltage

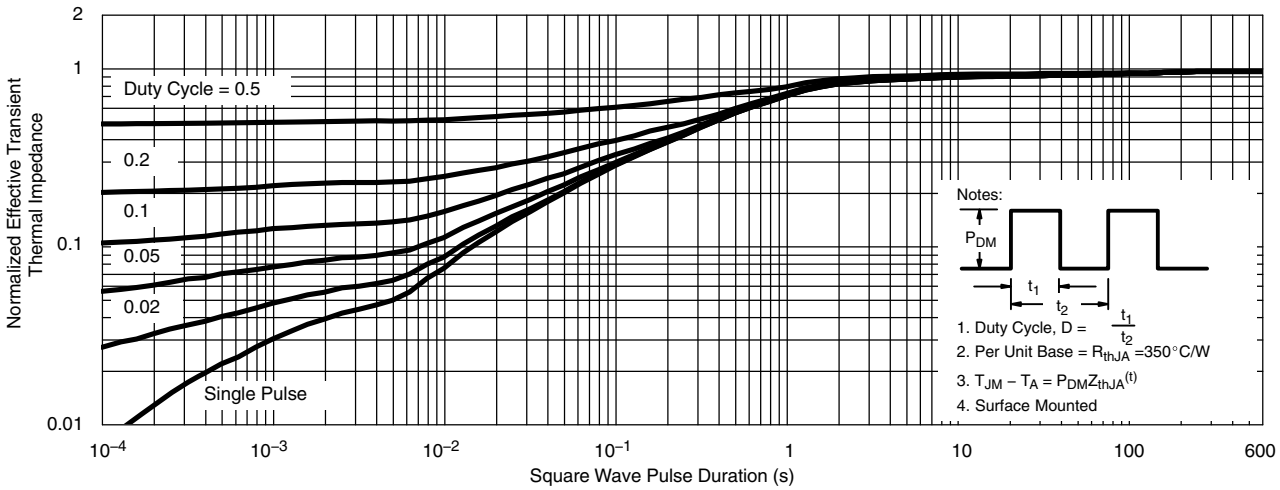


On-Resistance vs. Gate-to-Source Voltage

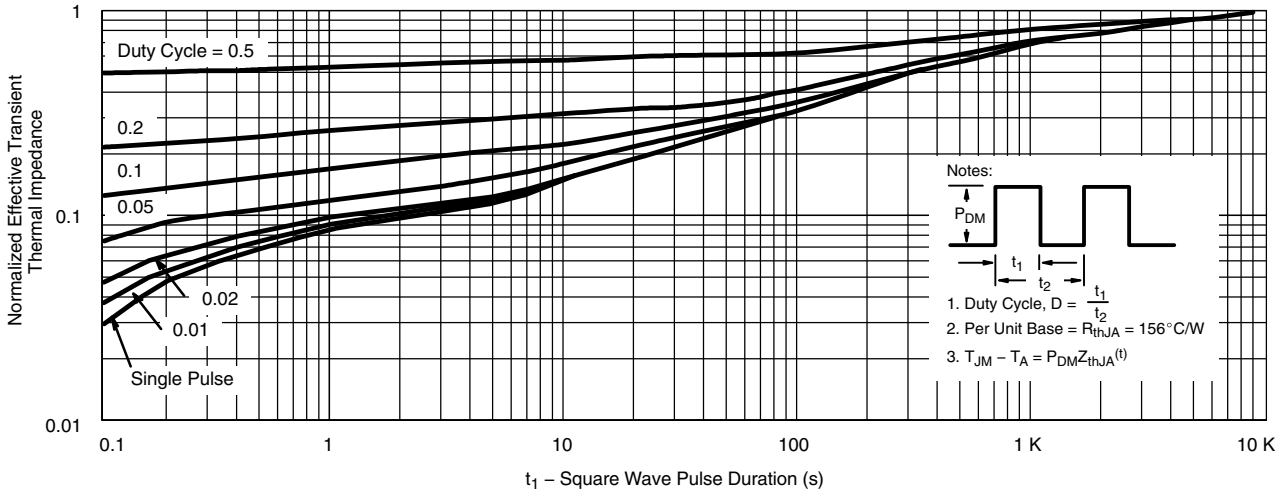


Threshold Voltage

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient
(TO-236, TN2404K only)



Normalized Thermal Transient Impedance, Junction-to-Ambient
(TO-226AA, TN2404KL and TO-92-18RM, BS107KL only)

Disclaimer

All products due to improve reliability, function or design or for other reasons, product specifications and data are subject to change without notice.

Taiwan VBsemi Electronics Co., Ltd., branches, agents, employees, and all persons acting on its or their representatives (collectively, the "Taiwan VBsemi"), assumes no responsibility for any errors, inaccuracies or incomplete data contained in the table or any other any disclosure of any information related to the product.(www.VBsemi.com)

Taiwan VBsemi makes no guarantee, representation or warranty on the product for any particular purpose of any goods or continuous production. To the maximum extent permitted by applicable law on Taiwan VBsemi relinquished: (1) any application and all liability arising out of or use of any products; (2) any and all liability, including but not limited to special, consequential damages or incidental ; (3) any and all implied warranties, including a particular purpose, non-infringement and merchantability guarantee.

Statement on certain types of applications are based on knowledge of the product is often used in a typical application of the general product VBsemi Taiwan demand that the Taiwan VBsemi of. Statement on whether the product is suitable for a particular application is non-binding. It is the customer's responsibility to verify specific product features in the products described in the specification is appropriate for use in a particular application. Parameter data sheets and technical specifications can be provided may vary depending on the application and performance over time. All operating parameters, including typical parameters must be made by customer's technical experts validated for each customer application. Product specifications do not expand or modify Taiwan VBsemi purchasing terms and conditions, including but not limited to warranty herein.

Unless expressly stated in writing, Taiwan VBsemi products are not intended for use in medical, life saving, or life sustaining applications or any other application. Wherein VBsemi product failure could lead to personal injury or death, use or sale of products used in Taiwan VBsemi such applications using client did not express their own risk. Contact your authorized Taiwan VBsemi people who are related to product design applications and other terms and conditions in writing.

The information provided in this document and the company's products without a license, express or implied, by estoppel or otherwise, to any intellectual property rights granted to the VBsemi act or document. Product names and trademarks referred to herein are trademarks of their respective representatives will be all.

Material Category Policy

Taiwan VBsemi Electronics Co., Ltd., hereby certify that all of the products are determined to be oHS compliant and meets the definition of restrictions under Directive of the European Parliament 2011/65 / EU, 2011 Nian. 6. 8 Ri Yue restrict the use of certain hazardous substances in electrical and electronic equipment (EEE) - modification, unless otherwise specified as inconsistent.(www.VBsemi.com)

Please note that some documents may still refer to Taiwan VBsemi RoHS Directive 2002/95 / EC. We confirm that all products identified as consistent with the Directive 2002/95 / EC European Directive 2011/65 /.

Taiwan VBsemi Electronics Co., Ltd. hereby certify that all of its products comply identified as halogen-free halogen-free standards required by the JEDEC JS709A. Please note that some Taiwanese VBsemi documents still refer to the definition of IEC 61249-2-21, and we are sure that all products conform to confirm compliance with IEC 61249-2-21 standard level JS709A.